

# ZXMN6A11ZTA-P

#### **N-Channel Enhancement Mode MOSFET**

www.sot23.com.tw

#### **Features**

- $V_{DS}$  =60V, $I_D$  =3.5A  $R_{DS(ON)}$  <100mΩ @  $V_{GS}$ =10V  $R_{DS(ON)}$  < 120mΩ @  $V_{GS}$ =4.5V
- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

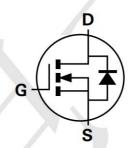
#### **Application**

- · Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

## Package and Pin Configuration

SOT89-3





Marking: P 603N

Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	3.5	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	10	Α
Maximum Power Dissipation	P <sub>D</sub>	1.7	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	73.5	°C/W
--	------	------



# N-Channel Enhancement Mode MOSFET

www.sot23.com.tw

# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	mbol Condition		Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60	-		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	/ -	-	1	μΑ
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	/-	±100	nA
On Characteristics (Note 3)	,					100
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	1		2.3	V
Drain-Source On-State Resistance	В	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	\-\	62		mΩ
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	- \	-	120	mΩ
Forward Transconductance	<b>g</b> FS	$V_{DS}$ =15 $V$ , $I_{D}$ =2 $A$	2	-	-	S
Dynamic Characteristics (Note4)			,			-
Input Capacitance	C <sub>Iss</sub>	)/ -20\/\/ -0\/	-	247	-	PF
Output Capacitance	Coss	$V_{DS}$ =30V, $V_{GS}$ =0V, F=1.0MHz		34	1-1	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0WHZ		19.5	-	PF
Switching Characteristics (Note 4)			•			-
Turn-on Delay Time	t <sub>d(on)</sub>	$\lambda$	#0	6	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =30V,I <sub>D</sub> =1.5A	-	15	8	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GS}}\text{=}10\text{V}, R_{\text{GEN}}\text{=}1\Omega$	-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg	V 00V/1 0A	-	6	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =30V,I <sub>D</sub> =3A,	=0	1	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =4.5V	-	1.3	8	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	$V_{GS}$ =0 $V$ , $I_{S}$ =3 $A$	-	EI	1.2	V
Diode Forward Current (Note 2)	Is			-	3	Α

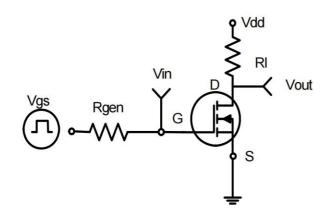




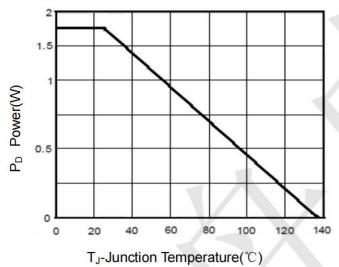
### **N-Channel Enhancement Mode MOSFET**

www.sot23.com.tw

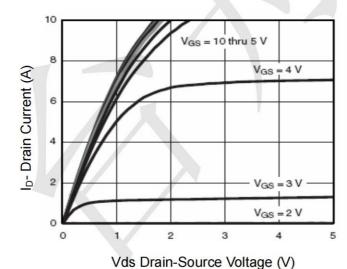
# **Typical Characteristics**



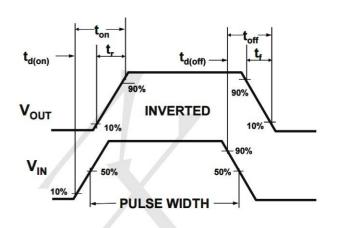
**Figure 1 Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 



**Figure 2 Switching Waveforms** 

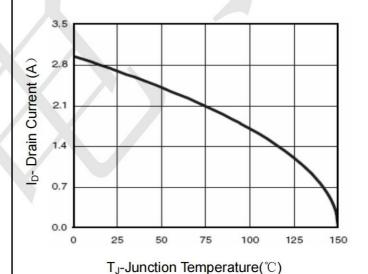


Figure 4 Drain Current

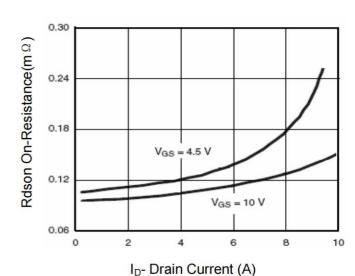


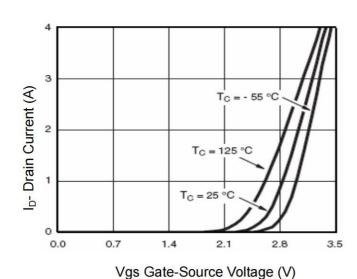
Figure 6 Drain-Source On-Resistance



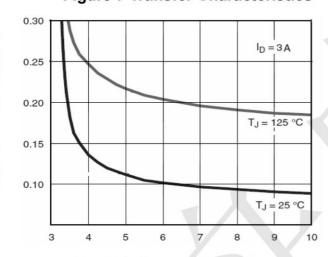


#### **N-Channel Enhancement Mode MOSFET**

### www.sot23.com.tw



**Figure 7 Transfer Characteristics** 



Rdson On-Resistance( ()

Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

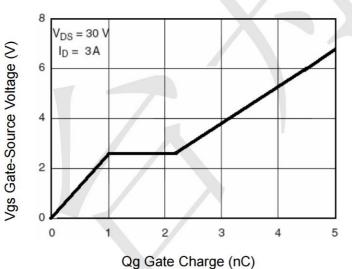


Figure 11 Gate Charge

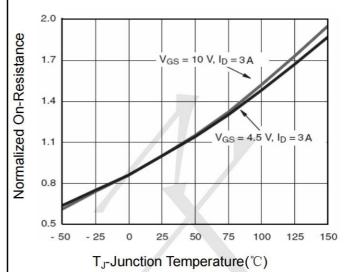


Figure 8 Drain-Source On-Resistance

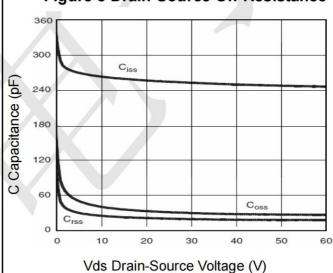


Figure 10 Capacitance vs Vds

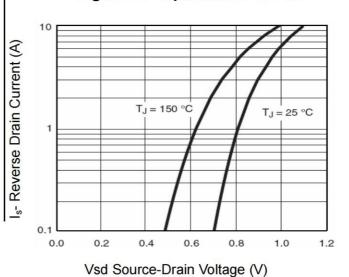


Figure 12 Source- Drain Diode Forward







www.sot23.com.tw

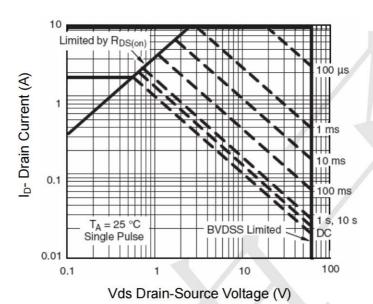


Figure 13 Safe Operation Area

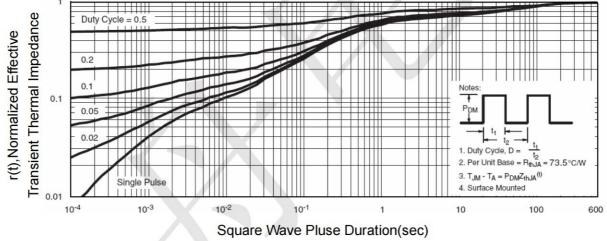
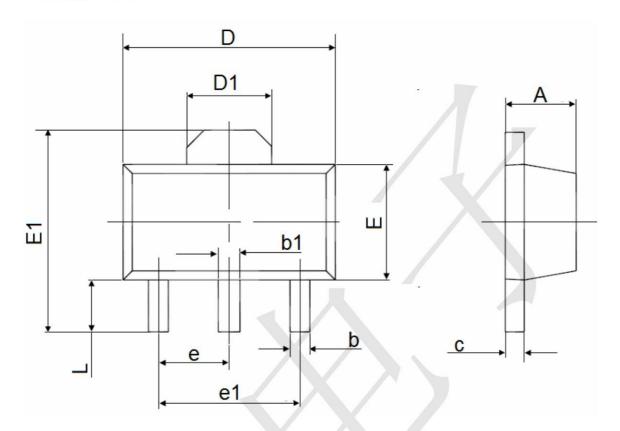


Figure 14 Normalized Maximum Transient Thermal Impedance



www.sot23.com.tw

# SOT-89-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1 -	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550 REF.		0.061 REF.		
E	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP.		0.060 TYP.		
e1	3.000 TYP.		0.118 TYP.		
L	0.900	1.200	0.035	0.047	

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by TECH PUBLIC manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 IRFF430 JANTX2N5237 2N7000 FCA20N60\_F109 FDZ595PZ AOD464 2SK2267(Q) 2SK2545(Q,T)
405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C BSC884N03MS G BSF024N03LT3 G
PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7
SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6
C3M0021120D DMN13M9UCA6-7 BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IRF40SC240ARMA1
IPS60R1K0PFD7SAKMA1